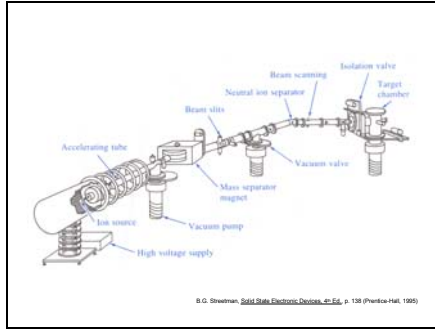
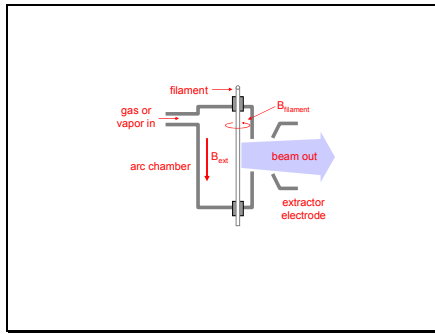


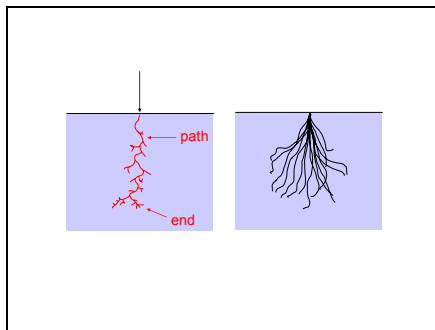
Slide 60



Slide 61



Slide 62

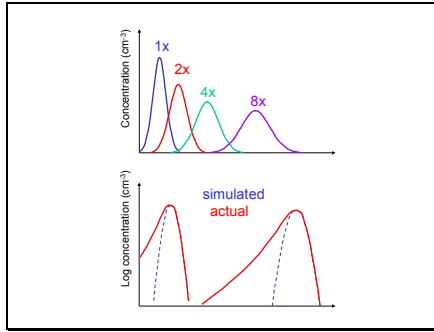


Slide 63

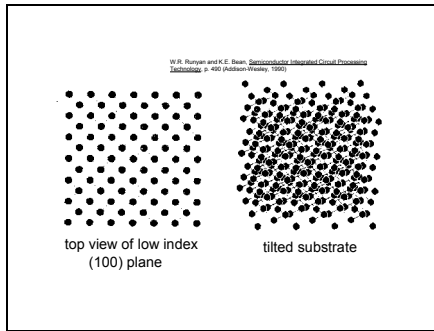
Energy (KeV)	P in Si		P in SiO <sub>2</sub>		B in Si		B in SiO <sub>2</sub>	
	Rp	ΔRp	Rp	ΔRp	Rp	ΔRp	Rp	ΔRp
10	0.0139	0.0069	0.0108	0.0048	0.0333	0.0171	0.0298	0.0143
20	0.0253	0.0119	0.0199	0.0084	0.0662	0.0383	0.0622	0.0325
30	0.0368	0.0166	0.0292	0.0119	0.0987	0.0531	0.0954	0.0442
40	0.0486	0.0212	0.0388	0.0152	0.1302	0.0443	0.1263	0.0418
50	0.0607	0.0256	0.0486	0.0185	0.1628	0.0504	0.1606	0.0483
60	0.0730	0.0298	0.0586	0.0216	0.1903	0.0566	0.1921	0.0640
70	0.0855	0.0340	0.0688	0.0247	0.2188	0.0601	0.2229	0.0690
80	0.0981	0.0380	0.0792	0.0276	0.2485	0.0641	0.2628	0.0634
90	0.1109	0.0418	0.0896	0.0305	0.2733	0.0677	0.2819	0.0674
100	0.1238	0.0456	0.1002	0.0333	0.2984	0.0710	0.3104	0.0710
110	0.1367	0.0492	0.1108	0.0361	0.3248	0.0739	0.3382	0.0743
120	0.1497	0.0526	0.1215	0.0387	0.3496	0.0766	0.3653	0.0774
130	0.1627	0.0562	0.132	0.0412	0.3737	0.0790	0.3919	0.0801
140	0.1727	0.0595	0.1429	0.0437	0.3974	0.0813	0.4179	0.0827
160	0.1888	0.0628	0.1537	0.0461	0.4205	0.0834	0.4434	0.0851

J.F. Gibbons, W.D. Johnson, and S.W. Myrick, *Differential Scattering Analysis, Semiconductors and Related Materials*, 22, 24, p. 378 (Sturbridge, Connecticut, Hutchinson and Ross, 1975 reprinted © by John Wiley & Sons)

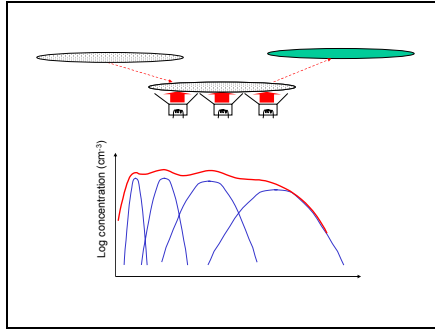
Slide 64



Slide 65



Slide 66



Slide 67

